

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC5066FT

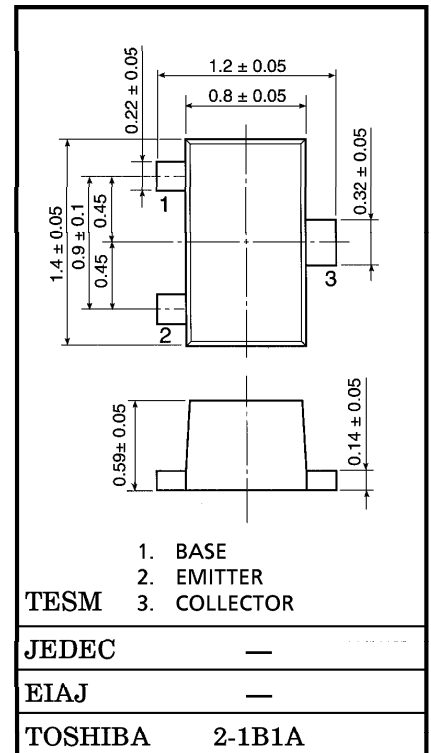
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Unit in mm

- Low Noise Figure, High Gain.
- $NF=1.1dB, |S_{21e}|^2=12dB (f=1GHz)$

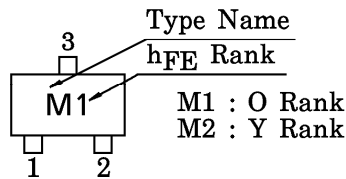
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	20	V
Collector-Emitter Voltage	V _{CE0}	12	V
Emitter-Base Voltage	V _{EB0}	3	V
Base Current	I _B	15	mA
Collector Current	I _C	30	mA
Collector Power Dissipation	P _C	100	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



Weight : 0.0022g

MARKING



MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f _T	V _{CE} =5V, I _C =10mA	5	7	—	GHz
Insertion Gain	S _{21e} ² (1)	V _{CE} =5V, I _C =10mA, f=500MHz	—	17	—	dB
	S _{21e} ² (2)	V _{CE} =5V, I _C =10mA, f=1GHz	8.5	12	—	
Noise Figure	NF (1)	V _{CE} =5V, I _C =3mA, f=500MHz	—	1	—	dB
	NF (2)	V _{CE} =5V, I _C =3mA, f=1GHz	—	1.1	2.0	

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=10V, I_E=0$	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=1V, I_C=0$	—	—	1	μA
DC Current Gain	h_{FE} (Note 1)	$V_{CE}=5V, I_C=10mA$	80	—	240	—
Output Capacitance	C_{ob}	$V_{CB}=5V, I_E=0, f=1MHz$ (Note 2)	—	0.7	—	pF
Reverse Transfer Capacitance	C_{re}		—	0.45	0.9	pF

(Note 1) : h_{FE} Classification O : 80~160, Y : 120~240

(Note 2) : C_{re} is measured by 3 terminal method with capacitance bridge.